

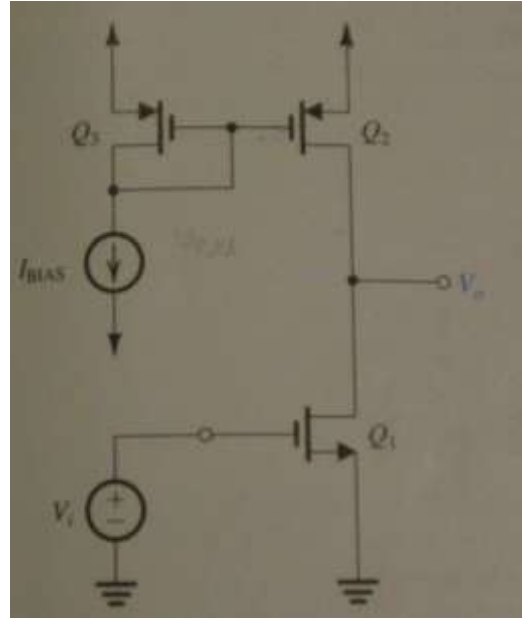
# Electronics II midterm exam

1.(18%) Figure 1 shows a CMOS amplifier. The dc bias current is 100  $\mu$ A. For  $Q_1$ ,  $\mu_n C_{ox} = 90 \mu\text{A/V}^2$ ,  $V_A = 12.8\text{V}$ ,  $W/L = 100 \mu\text{m}/1.6 \mu\text{m}$ . For  $Q_2$ ,  $|V_A| = 19.2\text{V}$ .

1. Find the low-frequency gain of the amplifier. (9%)

2. If  $C_L = 1\text{pF}$  dominates the high frequency pole, find the high 3-dB frequency of the amplifier. (9%)

Figure 1: a pair of PMOSs work as a current mirror pair( $Q_2$ ), and a NMOS with its drain connected to the drain of PMOS  $Q_2$ .  $v_o$  is the drain voltage.  $v_i$  is insert from the gate of  $Q_1$ . the sources of PMOSs are connected to a constant voltage supply and the source of NMOS is grounded.



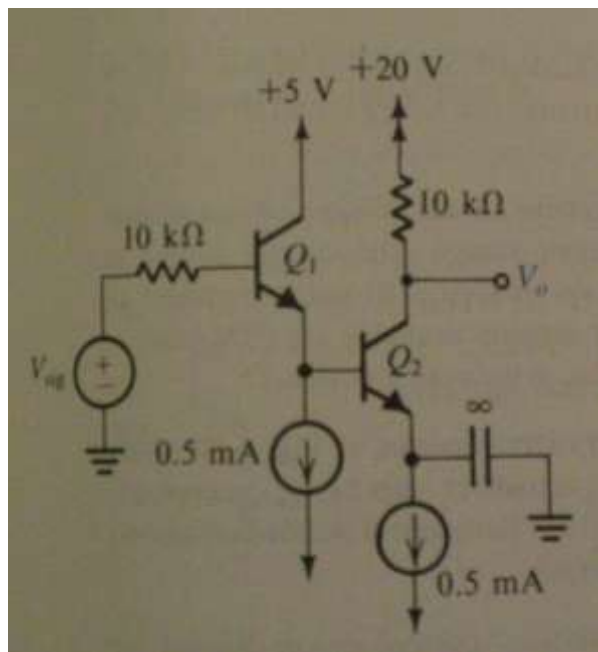
2.(14%) For the BJT cascade amplifier shown above in Figure 2, let  $\beta = 100$ ,  $C_\mu = 2\text{pF}$ , and  $C_\pi = 6\text{pF}$ . Neglect  $r_x$  and  $r_o$ . Using any method you like,

1. (7%) estimate the midband gain  $A_M$  and

2. (7%) find the 3dB frequency  $f_H$ .

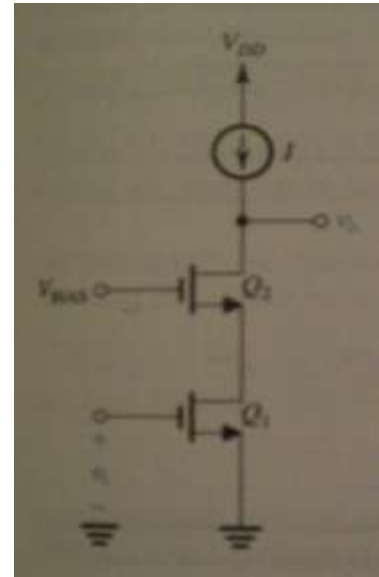
Errors on the order of 10% or 20% are acceptable, as long as your concept is correct.

Figure 2:  $R_{sig} = 10\text{k}$ ,  $R$  in the drain of  $Q_2$  is  $10\text{k}$ , and current source in both emitters are  $0.5\text{mA}$ . The emitter of  $Q_2$  is with bypassing capacitance.



3.(18%) For the MOS cascode amplifier shown in Fig.3.

1. Describe its advantages and disadvantages. (9%)
2. Provide proof of your statement in (1).(9%)



4.(18%) A common-source amplifier has  $g_m = 2\text{mA/V}$ ,  $r_o = 50\text{k}\Omega$ ,  $\lambda = 0.2$ , and  $R_L = 50\text{k}\Omega$  has a  $500\Omega$  resistance connected in the source lead. Find

1. (4%)  $R_{out}$
2. (3%)  $A_{vo}$
3. (3%)  $A_v$
4. (4%)  $G_v$ , and
5. (4%) the fraction of  $v_i$  that appears between gate and source.

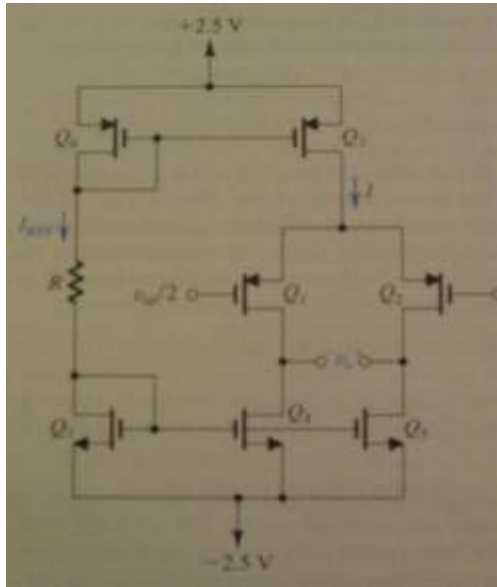
5.(14%) For the MOS differential amplifier with active loads shown in Fig. 5,

1. (7%) find  $V_{SG}$  for  $Q_1$  and  $Q_2$  and
2. (7%) calculate the differential voltage gain  $A_d$ .

Let  $I_{REF} = 90\mu\text{A}$ ,  $V_{tn} = 0.7\text{V}$ ,  $V_{tp} = -0.8\text{V}$ ,  $\mu_n C_{ox} = 160\mu\text{A/V}^2$ ,  $\mu_p C_{ox} = 40\mu\text{A/V}^2$ ,  $|V_A|(\text{for all devices}) = 10\text{V}$ . The device geometrics are given below in  $\mu\text{m}$ :

	$Q_1$	$Q_2$	$Q_3$	$Q_4$	$Q_5$	$Q_6$
W/L	20/0.8	10/0.8	40/0.8	5/0.8	5/0.8	40/0.8

Figure 5: As the problem in the textbook. Current mirror utilizing PMOS for three node of the differential amplifier. the drains of the DA are also current mirrors, utilizing steering



- 6.(18%) For the MOS differential amplifier shown above in Fig.6, where  $R_{ss}$  is the internal resistance of the current source, derive
1. (9%) the input DC offset voltage ( $V_{os}$ ), and
  2. (9%) the common-mode rejection ratio in the presence of resistance mismatch ( $R_D$ ). Assume that the two transistors are perfectly matched (in solving the two sub-problems).

